

Bhera Ram Tak

List of Publications by Year in descending order

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Version: 2024-02-01

19
papers

596
citations

687220

13
h-index

839398

18
g-index

19
all docs

19
docs citations

19
times ranked

537
citing authors

#	ARTICLE	IF	CITATIONS
1	Electronic excitation-induced tunneling and charge-trapping explored by in situ electrical characterization in Ni/HfO ₂ /Î ² -Ga ₂ O ₃ metal-oxide semiconductor capacitors. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2022, 281, 115716.	1.7	6
2	Wide range temperature-dependent (80-630 K) study of Hall effect and the Seebeck coefficient of Î ² -Ga ₂ O ₃ single crystals. <i>Applied Physics Letters</i> , 2021, 118, .	1.5	9
3	Ultra-Low Noise and Self-Powered Î ² -Ga ₂ O ₃ Deep Ultraviolet Photodetector Array with Large Linear Dynamic Range. <i>ACS Applied Electronic Materials</i> , 2021, 3, 2145-2151.	2.0	25
4	Deep-Level Traps Responsible for Persistent Photocurrent in Pulsed-Laser-Deposited Î ² -Ga ₂ O ₃ Thin Films. <i>Crystals</i> , 2021, 11, 1046.	1.0	9
5	Recent advances in the growth of gallium oxide thin films employing various growth techniques—a review. <i>Journal Physics D: Applied Physics</i> , 2021, 54, 453002.	1.3	68
6	Temperature-Driven Perturbations in Growth Kinetics, Structural and Optical Properties of NiO Thin Films. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2021, 218, 2100241.	0.8	5
7	Swift heavy ion irradiation-induced modifications in the electrical and surface properties of Î ² -Ga ₂ O ₃ . <i>Applied Physics Letters</i> , 2020, 117, .	1.5	27
8	Photovoltaic and flexible deep ultraviolet wavelength detector based on novel Î ² -Ga ₂ O ₃ /muscovite heteroepitaxy. <i>Scientific Reports</i> , 2020, 10, 16098.	1.6	32
9	Temperature-Dependent Electrical Characteristics of Ni/Au Vertical Schottky Barrier Diodes on Î ² -Ga ₂ O ₃ Epilayers. <i>ECS Journal of Solid State Science and Technology</i> , 2020, 9, 055004.	0.9	32
10	Radiation sustenance of HfO ₂ /Î ² -Ga ₂ O ₃ metal-oxide-semiconductor capacitors: gamma irradiation study. <i>Semiconductor Science and Technology</i> , 2020, 35, 055024.	1.0	16
11	Surface Modification of AlN Using Organic Molecular Layer for Improved Deep UV Photodetector Performance. <i>ACS Applied Electronic Materials</i> , 2020, 2, 739-746.	2.0	36
12	Wearable Gallium Oxide Solar-Blind Photodetectors on Muscovite Mica Having Ultrahigh Photoresponsivity and Detectivity with Added High-Temperature Functionalities. <i>ACS Applied Electronic Materials</i> , 2019, 1, 2463-2470.	2.0	48
13	Study of the photoresponse behavior of a high barrier Pd/MoS ₂ /Pd photodetector. <i>Journal Physics D: Applied Physics</i> , 2019, 52, 325102.	1.3	22
14	Enhanced Performance of MSM UV Photodetectors by Molecular Modification of Gallium Nitride Using Porphyrin Organic Molecules. <i>IEEE Transactions on Electron Devices</i> , 2019, 66, 2036-2039.	1.6	9
15	Giant UV Photoresponse of GaN-Based Photodetectors by Surface Modification Using Phenol-Functionalized Porphyrin Organic Molecules. <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 12017-12026.	4.0	59
16	High-temperature photocurrent mechanism of Î ² -Ga ₂ O ₃ based metal-semiconductor-metal solar-blind photodetectors. <i>Journal of Applied Physics</i> , 2019, 125, .	1.1	77
17	Gamma Irradiation Effect on Performance of Î ² -Ga ₂ O ₃ Metal-Semiconductor-Metal Solar-Blind Photodetectors for Space Applications. <i>ECS Journal of Solid State Science and Technology</i> , 2019, 8, Q3149-Q3153.	0.9	42
18	Point defects induced work function modulation of Î ² -Ga ₂ O ₃ . <i>Applied Surface Science</i> , 2019, 465, 973-978.	3.1	71

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19	Improvement in Self-Powered GaN-based Symmetric Metal-Semiconductor-Metal Ultraviolet Photodetectors by Using Phenol-Functionalized Porphyrin Organic Molecules. , 2018, , .		3